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a/s

O I P E 1201.63407

PATENT APPLICATION

AUG 11 2003

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

PATENT & TRADEMARK OFFICE
Applicant: Nayfeh et al.)
Serial No.: 09/496,506)
Conf. No.: 6344)
Filed: February 2, 2000)
For: SILICON NANOPARTICLE)
FIELD EFFECT TRANSISTOR)
AND TRANSISTOR MEMORY)
DEVICE)
Art Unit: 2811)
Examiner: Crane, Sara R.)
I hereby certify that this paper is being deposited with the
United States Postal Service as FIRST-CLASS mail in an
envelope addressed to: Mail Stop Non Fee Amendment,
Commissioner for Patents, P.O. Box 1450, Alexandria, VA
22313-1450, on this date.
Aug 6, 2003 Chris B. R.
Date F-CLASS.WCM Registration No. 43,874
Appr. February 20, 1998 Attorney for Applicant

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AMENDMENT E

Commissioner of Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

In response to the Office Action mailed May 6, 2003, please consider the following Remarks.

REMARKS

Claims 1-2 and 4-8 are currently pending. Claims 1-2 and 4-8 stand rejected under 35 U.S.C. § 112, first paragraph, as failing to comply with the enablement requirement. Particularly, the Office Action states that the claims "contain subject matter which was not described in the specification in such a way as to enable one skilled in the art to which it pertains, or with which it is most nearly connected, to make and/or use the invention."

Applicants respectfully traverse this rejection for at least the following reasons.